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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	dsPIC
Core Size	16-Bit
Speed	20 MIPS
Connectivity	CANbus, I²C, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, LVD, POR, PWM, WDT
Number of I/O	68
Program Memory Size	132KB (44K x 24)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	6K x 8
Voltage - Supply (Vcc/Vdd)	2.5V ~ 5.5V
Data Converters	A/D 16x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	80-TQFP
Supplier Device Package	80-TQFP (12x12)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/dspic30f6013at-20i-pt

5.5 Code Memory Programming

5.5.1 OVERVIEW

The Flash code memory array consists of 512 rows of thirty-two, 24-bit instructions. Each panel stores 16K instruction words, and each dsPIC30F device has either 1, 2 or 3 memory panels (see Table 5-2).

TABLE 5-2: DEVICE CODE MEMORY SIZE

Device	Code Size (24-bit Words)	Number of Rows	Number of Panels
dsPIC30F2010	4K	128	1
dsPIC30F2011	4K	128	1
dsPIC30F2012	4K	128	1
dsPIC30F3010	8K	256	1
dsPIC30F3011	8K	256	1
dsPIC30F3012	8K	256	1
dsPIC30F3013	8K	256	1
dsPIC30F3014	8K	256	1
dsPIC30F4011	16K	512	1
dsPIC30F4012	16K	512	1
dsPIC30F4013	16K	512	1
dsPIC30F5011	22K	704	2
dsPIC30F5013	22K	704	2
dsPIC30F5015	22K	704	2
dsPIC30F5016	22K	704	2
dsPIC30F6010	48K	1536	3
dsPIC30F6010A	48K	1536	3
dsPIC30F6011	44K	1408	3
dsPIC30F6011A	44K	1408	3
dsPIC30F6012	48K	1536	3
dsPIC30F6012A	48K	1536	3
dsPIC30F6013	44K	1408	3
dsPIC30F6013A	44K	1408	3
dsPIC30F6014	48K	1536	3
dsPIC30F6014A	48K	1536	3
dsPIC30F6015	48K	1536	3

5.5.2 PROGRAMMING METHODOLOGY

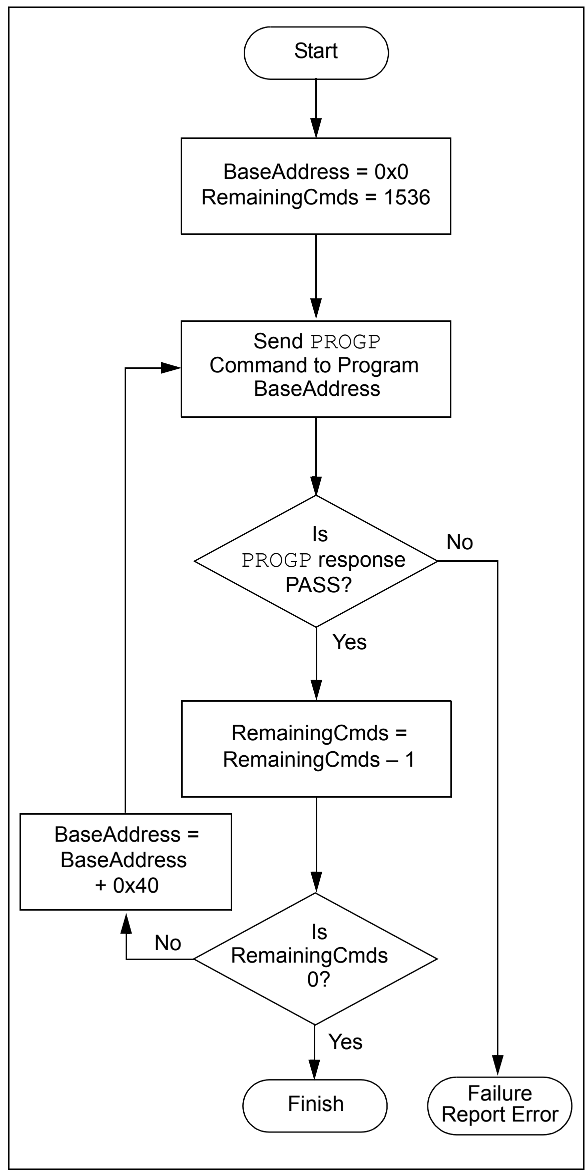
Code memory is programmed with the `PROGP` command. `PROGP` programs one row of code memory to the memory address specified in the command. The number of `PROGP` commands required to program a device depends on the number of rows that must be programmed in the device.

A flowchart for programming of code memory is illustrated in Figure 5-3. In this example, all 48K instruction words of a dsPIC30F6014A device are programmed. First, the number of commands to send (called 'RemainingCmds' in the flowchart) is set to 1536 and the destination address (called 'BaseAddress') is set to '0'.

Next, one row in the device is programmed with a `PROGP` command. Each `PROGP` command contains data for one row of code memory of the dsPIC30F6014A. After the first command is processed successfully, 'RemainingCmds' is decremented by 1 and compared to 0. Since there are more `PROGP` commands to send, 'BaseAddress' is incremented by 0x40 to point to the next row of memory.

On the second `PROGP` command, the second row of each memory panel is programmed. This process is repeated until the entire device is programmed. No special handling must be performed when a panel boundary is crossed.

FIGURE 5-3: FLOWCHART FOR PROGRAMMING dsPIC30F6014A CODE MEMORY



5.5.3 PROGRAMMING VERIFICATION

Once code memory is programmed, the contents of memory can be verified to ensure that programming was successful. Verification requires code memory to be read back and compared against the copy held in the programmer's buffer.

The READP command can be used to read back all the programmed code memory.

Alternatively, you can have the programmer perform the verification once the entire device is programmed using a checksum computation, as described in **Section 6.8 "Checksum Computation"**.

5.6 Data EEPROM Programming

5.6.1 OVERVIEW

The panel architecture for the data EEPROM memory array consists of 128 rows of sixteen 16-bit data words. Each panel stores 2K words. All devices have either one or no memory panels. Devices with data EEPROM provide either 512 words, 1024 words or 2048 words of memory on the one panel (see Table 5-3).

TABLE 5-3: DATA EEPROM SIZE

Device	Data EEPROM Size (Words)	Number of Rows
dsPIC30F2010	512	32
dsPIC30F2011	0	0
dsPIC30F2012	0	0
dsPIC30F3010	512	32
dsPIC30F3011	512	32
dsPIC30F3012	512	32
dsPIC30F3013	512	32
dsPIC30F3014	512	32
dsPIC30F4011	512	32
dsPIC30F4012	512	32
dsPIC30F4013	512	32
dsPIC30F5011	512	32
dsPIC30F5013	512	32
dsPIC30F5015	512	32
dsPIC30F5016	512	32
dsPIC30F6010	2048	128
dsPIC30F6010A	2048	128
dsPIC30F6011	1024	64
dsPIC30F6011A	1024	64
dsPIC30F6012	2048	128
dsPIC30F6012A	2048	128
dsPIC30F6013	1024	64
dsPIC30F6013A	1024	64
dsPIC30F6014	2048	128
dsPIC30F6014A	2048	128
dsPIC30F6015	2048	128

5.6.2 PROGRAMMING METHODOLOGY

The programming executive uses the PROGD command to program the data EEPROM. Figure 5-4 illustrates the flowchart of the process. Firstly, the number of rows to program (RemainingRows) is based on the device size, and the destination address (DestAddress) is set to '0'. In this example, 128 rows (2048 words) of data EEPROM will be programmed.

The first PROGD command programs the first row of data EEPROM. Once the command completes successfully, 'RemainingRows' is decremented by 1 and compared with 0. Since there are 127 more rows to program, 'BaseAddress' is incremented by 0x20 to point to the next row of data EEPROM. This process is then repeated until all 128 rows of data EEPROM are programmed.

FIGURE 5-4: FLOWCHART FOR PROGRAMMING dsPIC30F6014A DATA EEPROM

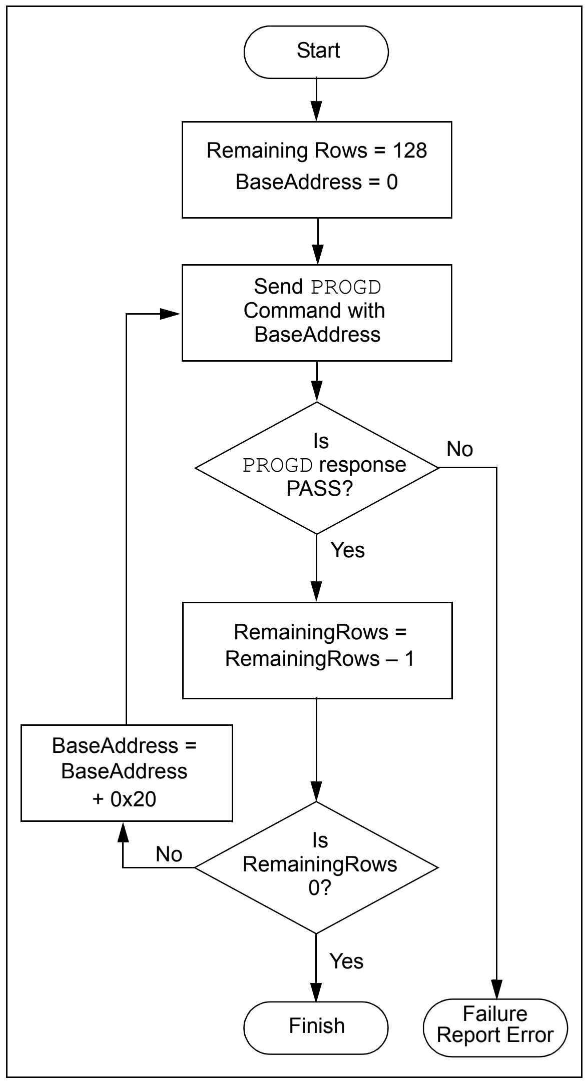


TABLE 5-6: FOSC CONFIGURATION BITS DESCRIPTION FOR dsPIC30F2011/2012, dsPIC30F3010/3011/3012/3013/3014, dsPIC30F4013, dsPIC30F5015/5016, dsPIC30F6010A/6011A/6012A/6013A/6014A AND dsPIC30F6015

Bit Field	Register	Description
FCKSM<1:0>	FOSC	**Clock Switching Mode** `1x` = Clock switching is disabled, Fail-Safe Clock Monitor is disabled `01` = Clock switching is enabled, Fail-Safe Clock Monitor is disabled `00` = Clock switching is enabled, Fail-Safe Clock Monitor is enabled
FOS<2:0>	FOSC	**Oscillator Source Selection on POR** `111` = Primary Oscillator `110` = Reserved `101` = Reserved `100` = Reserved `011` = Reserved `010` = Internal Low-Power RC Oscillator `001` = Internal Fast RC Oscillator (no PLL) `000` = Low-Power 32 kHz Oscillator (Timer1 Oscillator)
FPR<4:0>	FOSC	**Primary Oscillator Mode (when FOS<2:0> = `111b`)** `11xxx` = Reserved (do not use) `10111` = HS/3 w/PLL 16X – HS/3 crystal oscillator with 16X PLL (10 MHz-25 MHz crystal) `10110` = HS/3 w/PLL 8X – HS/3 crystal oscillator with 8X PLL (10 MHz-25 MHz crystal) `10101` = HS/3 w/PLL 4X – HS/3 crystal oscillator with 4X PLL (10 MHz-25 MHz crystal) `10100` = Reserved (do not use) `10011` = HS/2 w/PLL 16X – HS/2 crystal oscillator with 16X PLL (10 MHz-25 MHz crystal) `10010` = HS/2 w/PLL 8X – HS/2 crystal oscillator with 8X PLL (10 MHz-25 MHz crystal `10001` = HS/2 w/PLL 4X – HS/2 crystal oscillator with 4X PLL (10 MHz-25 MHz crystal) `10000` = Reserved (do not use) `01111` = ECIO w/PLL 16x – External clock with 16x PLL. OSC2 pin is I/O `01110` = ECIO w/PLL 8x – External clock with 8x PLL. OSC2 pin is I/O `01101` = ECIO w/PLL 4x – External clock with 4x PLL. OSC2 pin is I/O `01100` = Reserved (do not use) `01011` = Reserved (do not use) `01010` = FRC w/PLL 8x – Internal fast RC oscillator with 8x PLL. OSC2 pin is I/O `01001` = Reserved (do not use) `01000` = Reserved (do not use) `00111` = XT w/PLL 16X – XT crystal oscillator with 16X PLL `00110` = XT w/PLL 8X – XT crystal oscillator with 8X PLL `00101` = XT w/PLL 4X – XT crystal oscillator with 4X PLL `00100` = Reserved (do not use) `00011` = FRC w/PLL 16x – Internal fast RC oscillator with 8x PLL. OSC2 pin is I/O `00010` = Reserved (do not use) `00001` = FRC w/PLL 4x – Internal fast RC oscillator with 4x PLL. OSC2 pin is I/O `00000` = Reserved (do not use)

TABLE 5-7: CONFIGURATION BITS DESCRIPTION

Bit Field	Register	Description
FWPSA<1:0>	FWDT	**Watchdog Timer Prescaler A** 11 = 1:512 10 = 1:64 01 = 1:8 00 = 1:1
FWPSB<3:0>	FWDT	**Watchdog Timer Prescaler B** 1111 = 1:16 1110 = 1:15 • • • 0001 = 1:2 0000 = 1:1
FWDTEN	FWDT	**Watchdog Enable** 1 = Watchdog enabled (LPRC oscillator cannot be disabled. Clearing the SWDTEN bit in the RCON register will have no effect) 0 = Watchdog disabled (LPRC oscillator can be disabled by clearing the SWDTEN bit in the RCON register)
MCLREN	FBORPOR	**Master Clear Enable** 1 = Master Clear pin (MCLR) is enabled 0 = MCLR pin is disabled
PWMPIN	FBORPOR	**Motor Control PWM Module Pin Mode** 1 = PWM module pins controlled by PORT register at device Reset (tri-stated) 0 = PWM module pins controlled by PWM module at device Reset (configured as output pins)
HPOL	FBORPOR	**Motor Control PWM Module High-Side Polarity** 1 = PWM module high-side output pins have active-high output polarity 0 = PWM module high-side output pins have active-low output polarity
LPOL	FBORPOR	**Motor Control PWM Module Low-Side Polarity** 1 = PWM module low-side output pins have active-high output polarity 0 = PWM module low-side output pins have active-low output polarity
BOREN	FBORPOR	**PBOR Enable** 1 = PBOR enabled 0 = PBOR disabled
BORV<1:0>	FBORPOR	**Brown-out Voltage Select** 11 = 2.0V (not a valid operating selection) 10 = 2.7V 01 = 4.2V 00 = 4.5V
FPWRT<1:0>	FBORPOR	**Power-on Reset Timer Value Select** 11 = PWRT = 64 ms 10 = PWRT = 16 ms 01 = PWRT = 4 ms 00 = Power-up Timer disabled
RBS<1:0>	FBS	**Boot Segment Data RAM Code Protection (only present in dsPIC30F5011/5013/6010A/6011A/6012A/6013A/6014A/6015)** 11 = No Data RAM is reserved for Boot Segment 10 = Small-sized Boot RAM [128 bytes of RAM are reserved for Boot Segment] 01 = Medium-sized Boot RAM [256 bytes of RAM are reserved for Boot Segment] 00 = Large-sized Boot RAM [512 bytes of RAM are reserved for Boot Segment in dsPIC30F5011/5013, and 1024 bytes in dsPIC30F6010A/6011A/6012A/6013A/6014A/6015]

TABLE 5-10: dsPIC30F CONFIGURATION REGISTERS (FOR dsPIC30F2011/2012, dsPIC30F3010/3011/3012/3013/3014, dsPIC30F4013 AND dsPIC30F5015/5016)

Address	Name	Bit 15	Bit 14	Bit 13	Bit 12	Bit 11	Bit 10	Bit 9	Bit 8	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
0xF80000	FOSC	FCKSM<1:0>		—	—	—	FOS<2:0>			—	—	—	FPR<4:0>				
0xF80002	FWDT	FWDTEN	—	—	—	—	—	—	—	—	—	FWPSA<1:0>		FWPSB<3:0>			
0xF80004	FBORPOR	MCLREN	—	—	—	—	PWMPIN(1)	HPOL(1)	LPOL(1)	BOREN	—	BORV<1:0>		—	—	FPWRT<1:0>	
0xF80006	FBS	—	—	Reserved(2)		—	—	—	Reserved(2)	—	—	—	—	Reserved(2)			
0xF80008	FSS	—	—	Reserved(2)		—	—	Reserved(2)		—	—	—	—	Reserved(2)			
0xF8000A	FGS	—	—	—	—	—	—	—	—	—	—	—	—	—	Reserved(3)	GCP	GWRP
0xF8000C	FICD	BKBUG	COE	—	—	—	—	—	—	—	—	—	—	—	—	ICS<1:0>	

Note 1: On the 2011, 2012, 3012, 3013, 3014 and 4013, these bits are reserved (read as '1' and must be programmed as '1').
2: Reserved bits read as '1' and must be programmed as '1'.
3: The FGS<2> bit is a read-only copy of the GCP bit (FGS<1>).

TABLE 5-11: dsPIC30F CONFIGURATION REGISTERS (FOR dsPIC30F6010A/6011A/6012A/6013A/6014A AND dsPIC30F6015)

Address	Name	Bit 15	Bit 14	Bit 13	Bit 12	Bit 11	Bit 10	Bit 9	Bit 8	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
0xF80000	FOSC	FCKSM<1:0>		—	—	—	FOS<2:0>			—	—	—	FPR<4:0>				
0xF80002	FWDT	FWDTEN	—	—	—	—	—	—	—	—	—	FWPSA<1:0>		FWPSB<3:0>			
0xF80004	FBORPOR	MCLREN	—	—	—	—	PWMPIN(1)	HPOL(1)	LPOL(1)	BOREN	—	BORV<1:0>		—	—	FPWRT<1:0>	
0xF80006	FBS	—	—	RBS<1:0>		—	—	—	EBS	—	—	—	—	BSS<2:0>			BWRP
0xF80008	FSS	—	—	RSS<1:0>		—	—	ESS<1:0>		—	—	—	—	SSS<2:0>			SWRP
0xF8000A	FGS	—	—	—	—	—	—	—	—	—	—	—	—	—	GSS<1:0>		GWRP
0xF8000C	FICD	BKBUG	COE	—	—	—	—	—	—	—	—	—	—	—	—	ICS<1:0>	

Note 1: On the 6011A, 6012A, 6013A and 6014A, these bits are reserved (read as '1' and must be programmed as '1').

6.0 OTHER PROGRAMMING FEATURES

6.1 Erasing Memory

Memory is erased by using an ERASEB, ERASED or ERASEP command, as detailed in **Section 8.5 "Command Descriptions"**. Code memory can be erased by row using ERASEP. Data EEPROM can be erased by row using ERASED. When memory is erased, the affected memory locations are set to '1's.

ERASEB provides several Bulk Erase options. Performing a Chip Erase with the ERASEB command clears all code memory, data EEPROM and code protection registers. Alternatively, ERASEB can be used to selectively erase either all code memory or data EEPROM. Erase options are summarized in Table 6-1.

TABLE 6-1: ERASE OPTIONS

Command	Affected Region
ERASEB	Entire chip(1) or all code memory or all data EEPROM, or erase by segment
ERASED	Specified rows of data EEPROM
ERASEP(2)	Specified rows of code memory

Note 1: The system operation Configuration registers and device ID registers are not erasable.

2: ERASEP cannot be used to erase code-protect Configuration bits. These bits must be erased using ERASEB.

6.2 Modifying Memory

Instead of bulk-erasing the device before programming, it is possible that you may want to modify only a section of an already programmed device. In this situation, Chip Erase is not a realistic option.

Instead, you can erase selective rows of code memory and data EEPROM using ERASEP and ERASED, respectively. You can then reprogram the modified rows with the PROGP and PROGD command pairs. In these cases, when code memory is programmed, single-panel programming must be specified in the PROGP command.

For modification of Advanced Code Protection bits for a particular segment, the entire chip must first be erased with the ERASEB command. Alternatively, on devices that support Advanced Security, individual segments (code and/or data EEPROM) may be erased, by suitably changing the MS (Memory Select) field in the ERASEB command. The code-protect Configuration bits can then be reprogrammed using the PROGC command.

Note:	If read or write code protection is enabled for a segment, no modifications can be made to that segment until code protection is disabled. Code protection can only be disabled by performing a Chip Erase or by performing a Segment Erase operation for the required segment.

6.3 Reading Memory

The READD command reads the data EEPROM, Configuration bits and device ID of the device. This command only returns 16-bit data and operates on 16-bit registers. READD can be used to return the entire contents of data EEPROM.

The READP command reads the code memory of the device. This command only returns 24-bit data packed as described in **Section 8.3 "Packed Data Format"**. READP can be used to read up to 32K instruction words of code memory.

Note:	Reading an unimplemented memory location causes the programming executive to reset. All READD and READP commands **must** specify only valid memory locations.

6.4 Programming Executive Software Version

At times, it may be necessary to determine the version of programming executive stored in executive memory. The QVER command performs this function. See **Section 8.5.11 "QVER Command"** for more details about this command.

6.5 Data EEPROM Information in the Hexadecimal File

To allow portability of code, the programmer must read the data EEPROM information from the hexadecimal file. If data EEPROM information is not present, a simple warning message should be issued by the programmer. Similarly, when saving a hexadecimal file, all data EEPROM information must be included. An option to not include the data EEPROM information can be provided.

Microchip Technology Inc. believes that this feature is important for the benefit of the end customer.

8.5.3 READP COMMAND

15 — 12	11 — 8	7 — 0
Opcode	Length	
N		
Reserved		Addr_MSB
Addr_LS		

Field	Description
Opcode	0x2
Length	0x4
N	Number of 24-bit instructions to read (max of 32768)
Reserved	0x0
Addr_MSB	MSB of 24-bit source address
Addr_LS	LS 16 bits of 24-bit source address

The READP command instructs the programming executive to read N 24-bit words of code memory starting from the 24-bit address specified by Addr_MSB and Addr_LS. This command can only be used to read 24-bit data. All data returned in response to this command uses the packed data format described in **Section 8.3 "Packed Data Format"**.

Expected Response (2 + 3 * N/2 words for N even):
0x1200
2 + 3 * N/2
Least significant program memory word 1
...
Least significant data word N

Expected Response (4 + 3 * (N – 1)/2 words for N odd):
0x1200
4 + 3 * (N – 1)/2
Least significant program memory word 1
...
MSB of program memory word N (zero padded)

Note:	Reading unimplemented memory will cause the programming executive to reset.

8.5.4 PROGD COMMAND

15 — 12	11 — 8	7 — 0
Opcode	Length	
Reserved		Addr_MSB
Addr_LS		
D_1		
D_2		
...		
D_16		

Field	Description
Opcode	0x4
Length	0x13
Reserved	0x0
Addr_MSB	MSB of 24-bit destination address
Addr_LS	LS 16 bits of 24-bit destination address
D_1	16-bit data word 1
D_2	16-bit data word 2
...	16-bit data words 3 through 15
D_16	16-bit data word 16

The PROGD command instructs the programming executive to program one row of data EEPROM. The data to be programmed is specified by the 16 data words (D_1, D_2,..., D_16) and is programmed to the destination address specified by Addr_MSB and Addr_LSB. The destination address should be a multiple of 0x20.

Once the row of data EEPROM has been programmed, the programming executive verifies the programmed data against the data in the command.

Expected Response (2 words):
0x1400
0x0002

Note:	Refer to Table 5-3 for data EEPROM size information.

8.5.7 ERASEB COMMAND

15 12	11 2	0
Opcode	Length	
Reserved		MS

Field	Description
Opcode	0x7
Length	0x2
Reserved	0x0
MS	Select memory to erase: 0x0 = All Code in General Segment 0x1 = All Data EEPROM in General Segment 0x2 = All Code and Data EEPROM in General Segment, interrupt vectors and FGS Configuration register 0x3 = Full Chip Erase 0x4 = All Code and Data EEPROM in Boot, Secure and General Segments, and FBS, FSS and FGS Configuration registers 0x5 = All Code and Data EEPROM in Secure and General Segments, and FSS and FGS Configuration registers 0x6 = All Data EEPROM in Boot Segment 0x7 = All Data EEPROM in Secure Segment

The ERASEB command performs a Bulk Erase. The MS field selects the memory to be bulk erased, with options for erasing Code and/or Data EEPROM in individual memory segments.

When Full Chip Erase is selected, the following memory regions are erased:

- All code memory (even if code-protected)
- All data EEPROM
- All code-protect Configuration registers

Only the executive code memory, Unit ID, device ID and Configuration registers that are not code-protected remain intact after a Chip Erase.

Expected Response (2 words):
0x1700
0x0002

Note:	A Full Chip Erase cannot be performed in low-voltage programming systems (VDD less than 4.5 volts). ERASED and ERASEP must be used to erase code memory, executive memory and data memory. Alternatively, individual Segment Erase operations may be performed.

8.5.8 ERASED COMMAND

15 12	11 8	7 0
Opcode	Length	
Num_Rows		Addr_MSB
Addr_LS		

Field	Description
Opcode	0x8
Length	0x3
Num_Rows	Number of rows to erase (max of 128)
Addr_MSB	MSB of 24-bit base address
Addr_LS	LS 16 bits of 24-bit base address

The ERASED command erases the specified number of rows of data EEPROM from the specified base address. The specified base address must be a multiple of 0x20. Since the data EEPROM is mapped to program space, a 24-bit base address must be specified.

After the erase is performed, all targeted bytes of data EEPROM will contain 0xFF.

Expected Response (2 words):
0x1800
0x0002

Note:	The ERASED command cannot be used to erase the Configuration registers or device ID. Code-protect Configuration registers can only be erased with the ERASEB command, while the device ID is read-only.

8.5.9 ERASEP COMMAND

15–12	11–8	7–0
Opcode	Length	
Num_Rows		Addr_MSB
Addr_LS		

Field	Description
Opcode	0x9
Length	0x3
Num_Rows	Number of rows to erase
Addr_MSB	MSB of 24-bit base address
Addr_LS	LS 16 bits of 24-bit base address

The ERASEP command erases the specified number of rows of code memory from the specified base address. The specified base address must be a multiple of 0x40.

Once the erase is performed, all targeted words of code memory contain 0xFFFFFF.

Expected Response (2 words):
0x1900
0x0002

Note:	The ERASEP command cannot be used to erase the Configuration registers or device ID. Code-protect Configuration registers can only be erased with the ERASEB command, while the device ID is read-only.

8.5.10 QBLANK COMMAND

15–12	11–0
Opcode	Length
PSize	
Reserved	DSize

Field	Description
Opcode	0xA
Length	0x3
PSize	Length of program memory to check (in 24-bit words), max of 49152
Reserved	0x0
DSize	Length of data memory to check (in 16-bit words), max of 2048

The QBLANK command queries the programming executive to determine if the contents of code memory and data EEPROM are blank (contains all '1's). The size of code memory and data EEPROM to check must be specified in the command.

The Blank Check for code memory begins at 0x0 and advances toward larger addresses for the specified number of instruction words. The Blank Check for data EEPROM begins at 0x7FFFFE and advances toward smaller addresses for the specified number of data words.

QBLANK returns a QE_Code of 0xF0 if the specified code memory and data EEPROM are blank. Otherwise, QBLANK returns a QE_Code of 0x0F.

Expected Response (2 words for blank device):
0x1AF0
0x0002

Expected Response (2 words for non-blank device):
0x1A0F
0x0002

Note:	The QBLANK command does not check the system Configuration registers. The READD command must be used to determine the state of the Configuration registers.

9.2.3 QE_Code FIELD

The QE_Code is a byte in the first word of the response. This byte is used to return data for query commands, and error codes for all other commands.

When the programming executive processes one of the two query commands (QBLANK or QVER), the returned opcode is always PASS and the QE_Code holds the query response data. The format of the QE_Code for both queries is shown in Table 9-3.

TABLE 9-3: QE_Code FOR QUERIES

Query	QE_Code
QBLANK	0x0F = Code memory and data EEPROM are NOT blank 0xF0 = Code memory and data EEPROM are blank
QVER	0xMN, where programming executive software version = M.N (i.e., 0x32 means software version 3.2)

When the programming executive processes any command other than a Query, the QE_Code represents an error code. Supported error codes are shown in Table 9-4. If a command is successfully processed, the returned QE_Code is set to 0x0, which indicates that there was no error in the command processing. If the verify of the programming for the PROGD, PROGP or PROGC command fails, the QE_Code is set to 0x1. For all other programming executive errors, the QE_Code is 0x2.

TABLE 9-4: QE_Code FOR NON-QUERY COMMANDS

QE_Code	Description
0x0	No error
0x1	Verify failed
0x2	Other error

9.2.4 RESPONSE LENGTH

The response length indicates the length of the programming executive's response in 16-bit words. This field includes the 2 words of the response header.

With the exception of the response for the READD and READP commands, the length of each response is only 2 words.

The response to the READD command is N + 2 words, where N is the number of words specified in the READD command.

The response to the READP command uses the packed instruction word format described in **Section 8.3 "Packed Data Format"**. When reading an odd number of program memory words (N odd), the response to the READP command is (3 • (N + 1)/2 + 2) words. When reading an even number of program memory words (N even), the response to the READP command is (3 • N/2 + 2) words.

11.4 Flash Memory Programming in ICSP Mode

Programming in ICSP mode is described in **Section 11.4.1 "Programming Operations"** through **Section 11.4.3 "Starting and Stopping a Programming Cycle"**. Step-by-step procedures are described in **Section 11.5 "Erasing Program Memory in Normal-Voltage Systems"** through **Section 11.13 "Reading the Application ID Word"**. All programming operations must use serial execution, as described in **Section 11.2 "ICSP Operation"**.

11.4.1 PROGRAMMING OPERATIONS

Flash memory write and erase operations are controlled by the NVMCON register. Programming is performed by setting NVMCON to select the type of erase operation (Table 11-2) or write operation (Table 11-3), writing a key sequence to enable the programming and initiating the programming by setting the WR control bit, NVMCON<15>.

In ICSP mode, all programming operations are externally timed. An external 2 ms delay must be used between setting the WR control bit and clearing the WR control bit to complete the programming operation.

TABLE 11-2: NVMCON ERASE OPERATIONS

NVMCON Value	Erase Operation
0x407F	Erase all code memory, data memory (does not erase UNIT ID).
0x4075	Erase 1 row (16 words) of data EEPROM.
0x4074	Erase 1 word of data EEPROM.
0x4072	Erase all executive memory.
0x4071	Erase 1 row (32 instruction words) from 1 panel of code memory.
0x406E	Erase Boot Secure and General Segments, then erase FBS, FSS and FGS configuration registers.
0x4066	Erase all Data EEPROM allocated to Boot Segment.
0x405E	Erase Secure and General Segments, then erase FSS and FGS configuration registers.
0x4056	Erase all Data EEPROM allocated to Secure Segment.
0x404E	Erase General Segment, then erase FGS configuration register.
0x4046	Erase all Data EEPROM allocated to General Segment.

TABLE 11-3: NVMCON WRITE OPERATIONS

NVMCON Value	Write Operation
0x4008	Write 1 word to configuration memory.
0x4005	Write 1 row (16 words) to data memory.
0x4004	Write 1 word to data memory.
0x4001	Write 1 row (32 instruction words) into 1 panel of program memory.

11.4.2 UNLOCKING NVMCON FOR PROGRAMMING

Writes to the WR bit (NVMCON<15>) are locked to prevent accidental programming from taking place. Writing a key sequence to the NVMKEY register unlocks the WR bit and allows it to be written to. The unlock sequence is performed as follows:

```
MOV     #0x55, W8
MOV     W8, NVMKEY
MOV     #0xAA, W9
MOV     W9, NVMKEY
```

Note: Any working register, or working register pair, can be used to write the unlock sequence.

11.4.3 STARTING AND STOPPING A PROGRAMMING CYCLE

Once the unlock key sequence has been written to the NVMKEY register, the WR bit (NVMCON<15>) is used to start and stop an erase or write cycle. Setting the WR bit initiates the programming cycle. Clearing the WR bit terminates the programming cycle.

All erase and write cycles must be externally timed. An external delay must be used between setting and clearing the WR bit. Starting and stopping a programming cycle is performed as follows:

```
BSET    NVMCON, #WR
<Wait 2 ms>
BCLR    NVMCON, #WR
```

11.5 Erasing Program Memory in Normal-Voltage Systems

The procedure for erasing program memory (all code memory, data memory, executive memory and code-protect bits) consists of setting NVMCON to 0x407F, unlocking NVMCON for erasing and then executing the programming cycle. This method of bulk erasing program memory only works for systems where VDD is between 4.5 volts and 5.5 volts. The method for erasing program memory for systems with a lower VDD (3.0 volts-4.5 volts) is described in **Section 6.1 "Erasing Memory"**.

TABLE 11-4: SERIAL INSTRUCTION EXECUTION FOR BULK ERASING PROGRAM MEMORY (ONLY IN NORMAL-VOLTAGE SYSTEMS) (CONTINUED)

Command (Binary)	Data (Hexadecimal)	Description
0000	200558	`MOV #0x55, W8`
0000	883B38	`MOV W8, NVMKEY`
0000	200AA9	`MOV #0xAA, W9`
0000	883B39	`MOV W9, NVMKEY`
Step 11: Initiate the erase cycle.		
0000	A8E761	`BSET NVMCON, #WR`
0000	000000	`NOP`
0000	000000	`NOP`
—	—	`Externally time 'P13a' ms` (see **Section 13.0 "AC/DC Characteristics and Timing Requirements"**)
0000	000000	`NOP`
0000	000000	`NOP`
0000	A9E761	`BCLR NVMCON, #WR`
0000	000000	`NOP`
0000	000000	`NOP`

Note 1: Steps 2-8 are only required for the dsPIC30F5011/5013 devices. These steps may be skipped for all other devices in the dsPIC30F family.

TABLE 11-5: SERIAL INSTRUCTION EXECUTION FOR ERASING PROGRAM MEMORY (EITHER IN LOW-VOLTAGE OR NORMAL-VOLTAGE SYSTEMS) (CONTINUED)

Command (Binary)	Data (Hexadecimal)	Description
Step 18: Unlock the NVMCON to erase 1 row of data memory.		
0000	200558	`MOV #0x55, W8`
0000	883B38	`MOV W8, NVMKEY`
0000	200AA9	`MOV #0xAA, W9`
0000	883B39	`MOV W9, NVMKEY`
Step 19: Initiate the erase cycle.		
0000	A8E761	`BSET NVMCON, #WR`
0000	000000	`NOP`
0000	000000	`NOP`
—	—	`Externally time 'P13a' ms` (see **Section 13.0 "AC/DC Characteristics and Timing Requirements"**)
0000	000000	`NOP`
0000	000000	`NOP`
0000	A9E761	`BCLR NVMCON, #WR`
0000	000000	`NOP`
0000	000000	`NOP`
Step 20: Update the row address stored in NVMADR.		
0000	430307	`ADD W6, W7, W6`
0000	883B16	`MOV W6, NVMADR`
Step 21: Reset device internal PC.		
0000	040100	`GOTO 0x100`
0000	000000	`NOP`
Step 22: Repeat Steps 17-21 until all rows of data memory are erased.		

11.7 Writing Configuration Memory

The FOSC, FWDT, FBORPOR and FICD registers are not erasable. It is recommended that all Configuration registers be set to a default value after erasing program memory. The FWDT, FBORPOR and FICD registers can be set to a default all '1's value by programming 0xFFFF to each register. Since these registers contain unimplemented bits that read as '0' the default values shown in Table 11-6 will be read instead of 0xFFFF. The recommended default FOSC value is 0xC100, which selects the FRC clock oscillator setting.

The FGS, FBS and FSS Configuration registers are special since they enable code protection for the device. For security purposes, once any bit in these registers is programmed to '0' (to enable some code protection feature), it can only be set back to '1' by performing a Bulk Erase or Segment Erase as described in **Section 11.5 "Erasing Program Memory in Normal-Voltage Systems"**. Programming these bits from a '0' to '1' is not possible, but they may be programmed from a '1' to a '0' to enable code protection.

Table 11-7 shows the ICSP programming details for clearing the Configuration registers. In Step 1, the Reset vector is exited. In Step 2, the write pointer (W7) is loaded with 0x0000, which is the original destination address (in TBLPAG 0xF8 of program memory). In Step 3, the NVMCON is set to program one Configuration register. In Step 4, the TBLPAG register is initialized, to 0xF8, for writing to the Configuration registers. In Step 5, the value to write to the each Configuration register (0xFFFF) is loaded to W6. In Step 6, the Configuration register data is written to the write latch using the `TBLWTL` instruction. In Steps 7 and 8, the NVMCON is unlocked for programming and the programming cycle is initiated, as described in **Section 11.4 "Flash Memory Programming in ICSP Mode"**. In Step 9, the internal PC is set to 0x100 as a safety measure to prevent the PC from incrementing into unimplemented memory. Lastly, Steps 3-9 are repeated six times until all seven Configuration registers are cleared.

TABLE 11-6: DEFAULT CONFIGURATION REGISTER VALUES

Address	Register	Default Value
0xF80000	FOSC	0xC100
0xF80002	FWDT	0x803F
0xF80004	FBORPOR	0x87B3
0xF80006	FBS	0x310F
0xF80008	FSS	0x330F
0xF8000A	FGS	0x0007
0xF8000C	FICD	0xC003

TABLE 11-7: SERIAL INSTRUCTION EXECUTION FOR WRITING CONFIGURATION REGISTERS

Command (Binary)	Data (Hexadecimal)	Description
Step 1: Exit the Reset vector.		
0000 0000 0000	040100 040100 000000	GOTO 0x100 GOTO 0x100 NOP
Step 2: Initialize the write pointer (W7) for the `TBLWT` instruction.		
0000	200007	MOV #0x0000, W7
Step 3: Set the NVMCON to program 1 Configuration register.		
0000 0000	24008A 883B0A	MOV #0x4008, W10 MOV W10, NVMCON
Step 4: Initialize the TBLPAG register.		
0000 0000	200F80 880190	MOV #0xF8, W0 MOV W0, TBLPAG
Step 5: Load the Configuration register data to W6.		
0000 0000	2xxxx0 000000	MOV #<CONFIG_VALUE>, W0 NOP

11.9 Writing Data EEPROM

The procedure for writing data EEPROM is very similar to the procedure for writing code memory, except that fewer words are programmed in each operation. When writing data EEPROM, one row of data EEPROM is programmed at a time. Each row consists of sixteen 16-bit data words. Since fewer words are programmed during each operation, only working registers W0:W3 are used as temporary holding registers for the data to be programmed.

Table 11-9 shows the ICSP programming details for writing data EEPROM. Note that a different NVMCON value is required to write to data EEPROM, and that the TBLPAG register is hard-coded to 0x7F (the upper byte address of all locations of data EEPROM).

TABLE 11-9: SERIAL INSTRUCTION EXECUTION FOR WRITING DATA EEPROM

Command (Binary)	Data (Hexadecimal)	Description
Step 1: Exit the Reset vector.		
0000 0000 0000	040100 040100 000000	GOTO 0x100 GOTO 0x100 NOP
Step 2: Set the NVMCON to write 16 data words.		
0000 0000	24005A 883B0A	MOV #0x4005, W10 MOV W10, NVMCON
Step 3: Initialize the write pointer (W7) for `TBLWT` instruction.		

0000
0000
0000
	2007F0
	880190
	2xxxx7
		MOV #0x7F, W0
		MOV W0, TBLPAG
		MOV #<DestinationAddress15:0>, W7

Step 4: Load W0:W3 with the next 4 data words to program.		

0000
0000
0000
0000
	2xxxx0
	2xxxx1
	2xxxx2
	2xxxx3
		MOV #<WORD0>, W0
		MOV #<WORD1>, W1
		MOV #<WORD2>, W2
		MOV #<WORD3>, W3

Step 5: Set the read pointer (W6) and load the (next set of) write latches.		
0000 0000 0000 0000 0000 0000 0000 0000 0000 0000 0000 0000 0000 0000	EB0300 000000 BB1BB6 000000 000000 BB1BB6 000000 000000 BB1BB6 000000 000000 BB1BB6 000000 000000	CLR W6 NOP TBLWTL [W6++], [W7++] NOP NOP TBLWTL [W6++], [W7++] NOP NOP TBLWTL [W6++], [W7++] NOP NOP TBLWTL [W6++], [W7++] NOP NOP
Step 6: Repeat steps 4-5 four times to load the write latches for 16 data words.		

TABLE 11-10: SERIAL INSTRUCTION EXECUTION FOR READING CODE MEMORY (CONTINUED)

Command (Binary)	Data (Hexadecimal)	Description
Step 4: Output W0:W5 using the VISI register and REGOUT command.		
0000	883C20	MOV W0, VISI
0000	000000	NOP
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
0000	883C21	MOV W1, VISI
0000	000000	NOP
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
0000	883C22	MOV W2, VISI
0000	000000	NOP
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
0000	883C23	MOV W3, VISI
0000	000000	NOP
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
0000	883C24	MOV W4, VISI
0000	000000	NOP
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
0000	883C25	MOV W5, VISI
0000	000000	NOP
0001	<VISI>	Clock out contents of VISI register
0000	000000	NOP
Step 5: Reset the device internal PC.		
0000	040100	GOTO 0x100
0000	000000	NOP
Step 6: Repeat steps 3-5 until all desired code memory is read.		

12.2 Programming Verification

After the programming executive has been programmed to executive memory using ICSP, it must be verified. Verification is performed by reading out the contents of executive memory and comparing it with the image of the programming executive stored in the programmer.

Reading the contents of executive memory can be performed using the same technique described in **Section 11.10 "Reading Code Memory"**. A procedure for reading executive memory is shown in Table 12-2. Note that in Step 2, the TBLPAG register is set to 0x80 such that executive memory may be read.

TABLE 12-2: READING EXECUTIVE MEMORY

Command (Binary)	Data (Hexadecimal)	Description
Step 1: Exit the Reset vector.		

0000
0000
0000
	040100
	040100
	000000
		`GOTO 0x100`
		`GOTO 0x100`
		`NOP`

Step 2: Initialize `TBLPAG` and the read pointer (W6) for `TBLRD` instruction.		

0000
0000
0000
	200800
	880190
	EB0300
		`MOV #0x80, W0`
		`MOV W0, TBLPAG`
		`CLR W6`

Step 3: Initialize the write pointer (W7), and store the next four locations of executive memory to W0:W5.		

0000
0000
0000
0000
0000
0000
0000
0000
0000
0000
0000
0000
0000
0000
0000
0000
0000
0000
0000
0000
0000
0000
0000
0000
0000
0000
	EB0380
	000000
	BA1B96
	000000
	000000
	BADBB6
	000000
	000000
	BADBD6
	000000
	000000
	BA1BB6
	000000
	000000
	BA1B96
	000000
	000000
	BADBB6
	000000
	000000
	BADBD6
	000000
	000000
	BA1BB6
	000000
	000000
		`CLR W7`
		`NOP`
		`TBLRDL [W6], [W7++]`
		`NOP`
		`NOP`
		`TBLRDH.B [W6++], [W7++]`
		`NOP`
		`NOP`
		`TBLRDH.B [++W6], [W7++]`
		`NOP`
		`NOP`
		`TBLRDL [W6++], [W7++]`
		`NOP`
		`NOP`
		`TBLRDL [W6], [W7++]`
		`NOP`
		`NOP`
		`TBLRDH.B [W6++], [W7++]`
		`NOP`
		`NOP`
		`TBLRDH.B [++W6], [W7++]`
		`NOP`
		`NOP`
		`TBLRDL [W6++], [W7]`
		`NOP`
		`NOP`

TABLE A-1: CHECKSUM COMPUTATION (CONTINUED)

Device	Read Code Protection	Checksum Computation	Erased Value	Value with 0xAAAAAA at 0x0 and Last Code Address
dsPIC30F5016	Disabled	CFGB+SUM(0:00AFFF)	0xFC06	0xFA08
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6010	Disabled	CFGB+SUM(0:017FFF)	0xC406	0xC208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6010A	Disabled	CFGB+SUM(0:017FFF)	0xC406	0xC208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6011	Disabled	CFGB+SUM(0:015FFF)	0xF406	0xF208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6011A	Disabled	CFGB+SUM(0:015FFF)	0xF406	0xF208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6012	Disabled	CFGB+SUM(0:017FFF)	0xC406	0xC208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6012A	Disabled	CFGB+SUM(0:017FFF)	0xC406	0xC208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6013	Disabled	CFGB+SUM(0:015FFF)	0xF406	0xF208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6013A	Disabled	CFGB+SUM(0:015FFF)	0xF406	0xF208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6014	Disabled	CFGB+SUM(0:017FFF)	0xC406	0xC208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6014A	Disabled	CFGB+SUM(0:017FFF)	0xC406	0xC208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6015	Disabled	CFGB+SUM(0:017FFF)	0xC406	0xC208
	Enabled	CFGB	0x0404	0x0404

Item Description:

SUM(a:b) = Byte sum of locations a to b inclusive (all 3 bytes of code memory)

CFGB = **Configuration Block (masked)** = Byte sum of ((FOSC&0xC10F) + (FWDT&0x803F) + (FBORPOR&0x87B3) + (FBS&0x310F) + (FSS&0x330F) + (FGS&0x0007) + (FICD&0xC003))

APPENDIX B: HEX FILE FORMAT

Flash programmers process the standard HEX format used by the Microchip development tools. The format supported is the Intel® HEX 32 Format (INHX32). Please refer to Appendix A in the *"MPASM User's Guide"* (DS33014) for more information about hex file formats.

The basic format of the hex file is:

`:BBAAAATTHHHH...HHHHCC`

Each data record begins with a 9-character prefix and always ends with a 2-character checksum. All records begin with ':' regardless of the format. The individual elements are described below.

- `BB` - is a two-digit hexadecimal byte count representing the number of data bytes that appear on the line. Divide this number by two to get the number of words per line.
- `AAAA` - is a four-digit hexadecimal address representing the starting address of the data record. Format is high byte first followed by low byte. The address is doubled because this format only supports 8-bits. Divide the value by two to find the real device address.
- `TT` - is a two-digit record type that will be '00' for data records, '01' for end-of-file records and '04' for extended-address record.
- `HHHH` - is a four-digit hexadecimal data word. Format is low byte followed by high byte. There will be `BB`/2 data words following `TT`.
- `CC` - is a two-digit hexadecimal checksum that is the two's complement of the sum of all the preceding bytes in the line record.

Because the Intel hex file format is byte-oriented, and the 16-bit program counter is not, program memory sections require special treatment. Each 24-bit program word is extended to 32 bits by inserting a so-called "phantom byte". Each program memory address is multiplied by 2 to yield a byte address.

As an example, a section that is located at 0x100 in program memory will be represented in the hex file as 0x200.

The hex file will be produced with the following contents:

```
:020000040000fa
:040200003322110096
:00000001FF
```

Notice that the data record (line 2) has a load address of 0200, while the source code specified address 0x100. Note also that the data is represented in "little-endian" format, meaning the Least Significant Byte (LSB) appears first. The phantom byte appears last, just before the checksum.

APPENDIX C: REVISION HISTORY

Note: Revision histories were not recorded for revisions A through H. The previous revision (J), was published in August 2007.

Revision K (November 2010)

This version of the document includes the following updates:

- Added Note three to **Section 5.2 "Entering Enhanced ICSP Mode"**
- Updated the first paragraph of **Section 10.0 "Device ID"**
- Updated Table 10-1: Device IDs
- Removed the VARIANT bit and updated the bit definition for the DEVID register in Table 10-2: dsPIC30F Device ID Registers
- Removed the VARIANT bit and updated the bit field definition and description for the DEVID register in Table 10-3: Device ID Bits Description
- Updated Note 3 in **Section 11.3 "Entering ICSP Mode"**
- Updated Step 11 in Table 11-4: Serial Instruction Execution for BUlk Erasing Program Memory (Only in Normal-voltage Systems)
- Updated Steps 5, 12 and 19 in Table 11-5: Serial Instruction Execution for Erasing Program Memory (Either in Low-voltage or Normal-voltage Systems)
- Updated Steps 5, 6 and 8 in Table 11-7: Serial Instruction Execution for Writing Configuration Registers
- Updated Steps 6 and 8 in Table 11-8: Serial Instruction Execution for Writing Code Memory
- Updated Steps 6 and 8 in Table 11-9: Serial Instruction Execution for Writing Data EEPROM
- Updated Entering ICSP™ Mode (see Figure 11-4)
- Updated Steps 4 and 11 in Table 12-1: Programming the Programming Executive
- Renamed parameters: P12 to P12a and P13 to P13a, and added parameters P12b and P13b in Table 13-1: AC/DC Characteristics